

**Small Signal Schottky (double) diodes**

# BAT54S3/BAT54AS3

# BAT54CS3/BAT54SS3

**Description**

Planar silicon Schottky barrier diodes encapsulated in a SOT-323 very small plastic SMD package. Single diodes and double diodes with different pinning are available.

**Features**

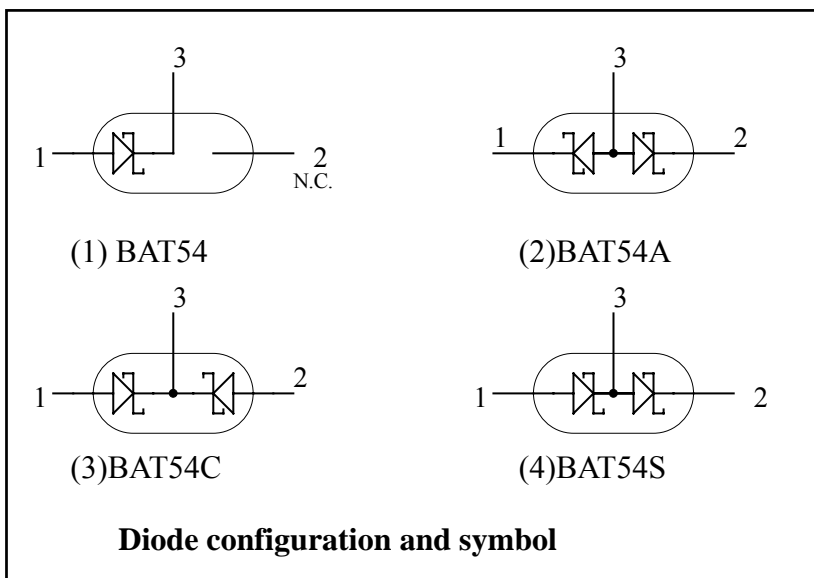
- Guard ring protected
- Low forward voltage drop
- Very small plastic SMD package
- Pb-free lead plating and halogen-free package

**Applications**

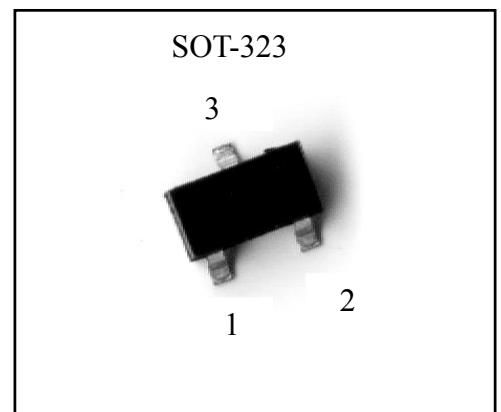
- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Blocking diodes

**Pinning**

Pin	Description			
	BAT54	BAT54A	BAT54C	BAT54S
1	A	K1	A1	A1
2	NC	K2	A2	K2
3	K	A1,A2	K1,K2	K1,A1



**Outline**



**Marking:**

Type	Marking Code
BAT54 S3	B4
BAT54AS3	B7
BAT54CS3	5C
BAT54SS3	B8



### Absolute Maximum Ratings

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
V <sub>R</sub>	continuous reverse voltage		-	30	V
I <sub>F</sub>	continuous forward current		-	200	mA
I <sub>FRM</sub>	repetitive peak forward current	tp≤1s, δ≤0.5	-	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	tp<10ms	-	600	mA
P <sub>tot</sub>	total power dissipation (per package)	T <sub>amb</sub> ≤25°C	-	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	operating junction temperature		-65	+150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

### Characteristics (Ta=25°C, unless otherwise specified)

Parameter	Symbol	Condition	Min.	Max.	Unit
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>R</sub> =100μA	30	-	V
Forward Voltage (Note 1)	V <sub>F</sub> (1)	I <sub>F</sub> =0.1mA	-	240	mV
	V <sub>F</sub> (2)	I <sub>F</sub> =1mA	-	320	mV
	V <sub>F</sub> (3)	I <sub>F</sub> =10mA	-	400	mV
	V <sub>F</sub> (4)	I <sub>F</sub> =30mA	-	500	mV
	V <sub>F</sub> (5)	I <sub>F</sub> =100mA	-	800	mV
Reverse Leakage Current (Note 2)	I <sub>R</sub>	V <sub>R</sub> =25V	-	2	μA
Diode Capacitance	C <sub>D</sub>	V <sub>R</sub> =1V, f=1MHz	-	10	pF
Reverse Recovery Time	trr	when switched from I <sub>F</sub> = 10mA to I <sub>R</sub> =10mA; R <sub>L</sub> =100Ω; measured at I <sub>R</sub> =1mA	-	5	ns

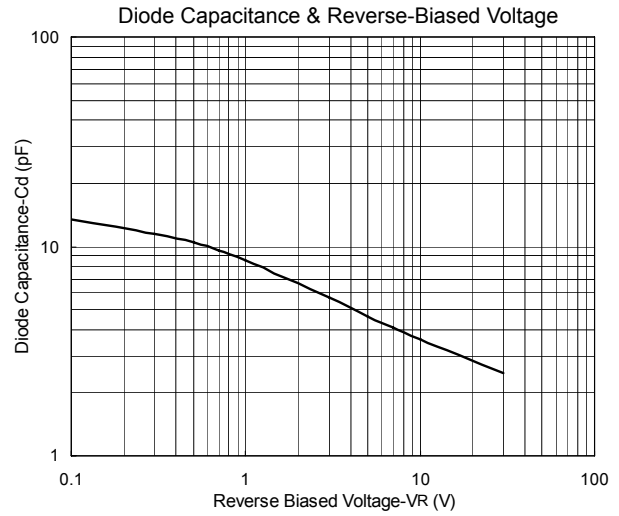
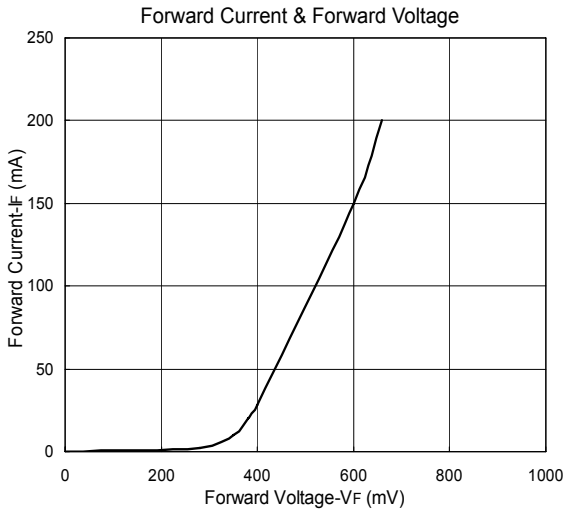
Notes: 1.pulse test, tp=380μs, duty cycle<2%.  
2.pulse test, tp=300μs, duty cycle<2%.

### Thermal Characteristics

Symbol	Parameter	Conditions	Value	Unit
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	625	K/W

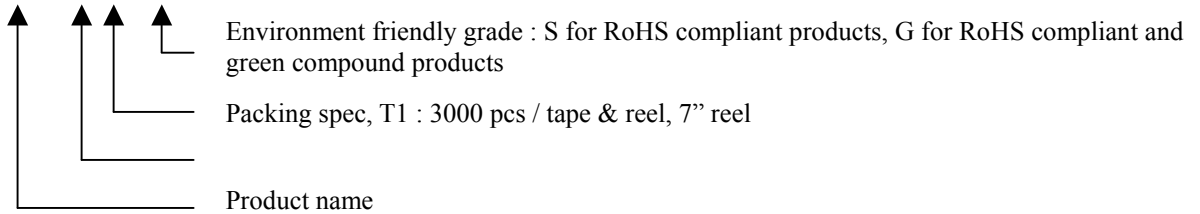
Note 1 : Refer to SOT-323 standard mounting conditions.

## Typical Characteristics

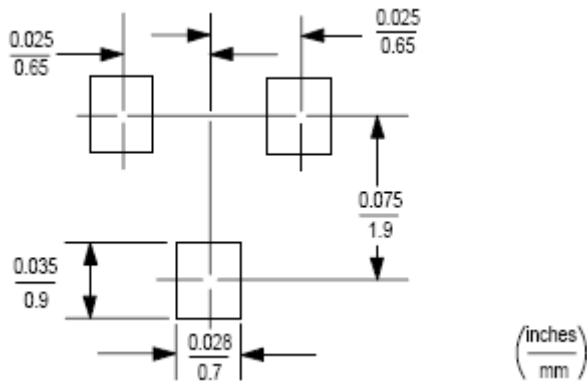


## Ordering Information

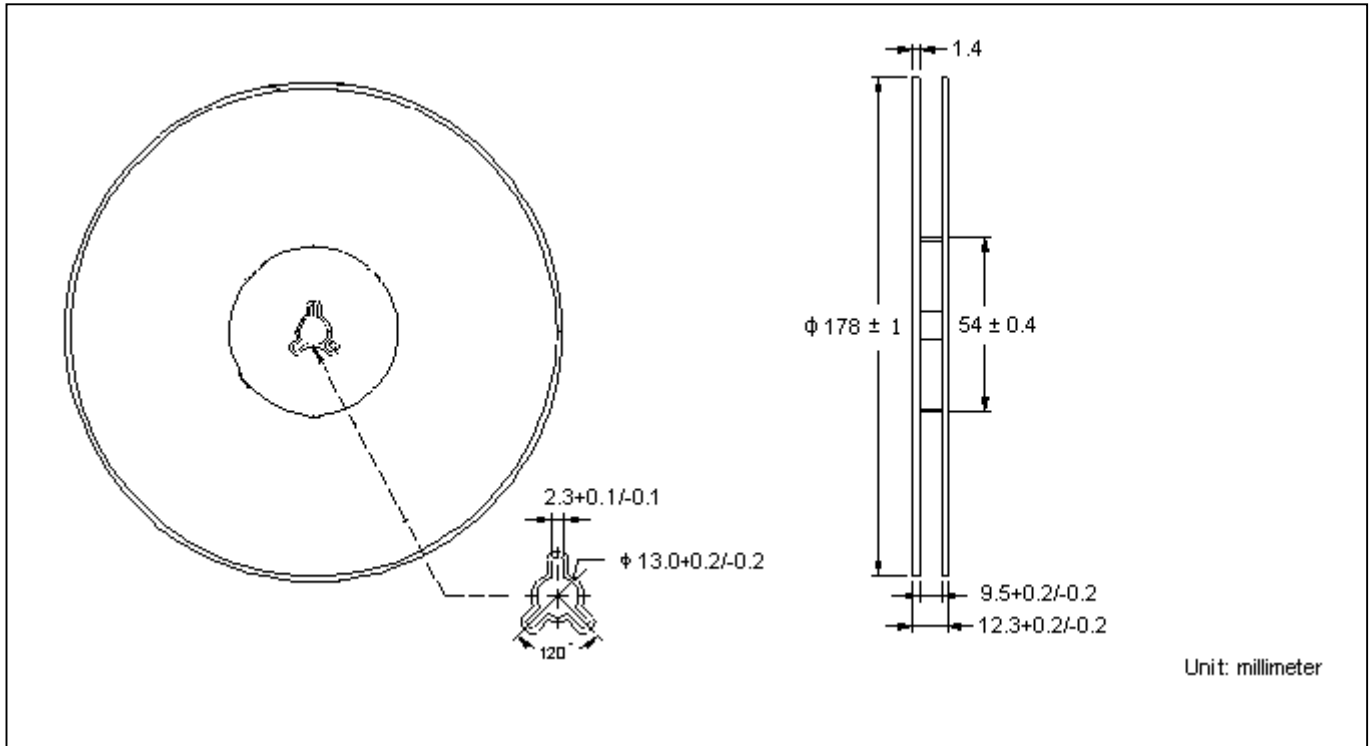
Device	Package	Shipping	Marking
BAT54S3-0-T1-G	SOT-323 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel	B4
BAT54AS3-0-T1-G			B7
BAT54CS3-0-T1-G			5C
BAT540SS3-0-T1-G			B8



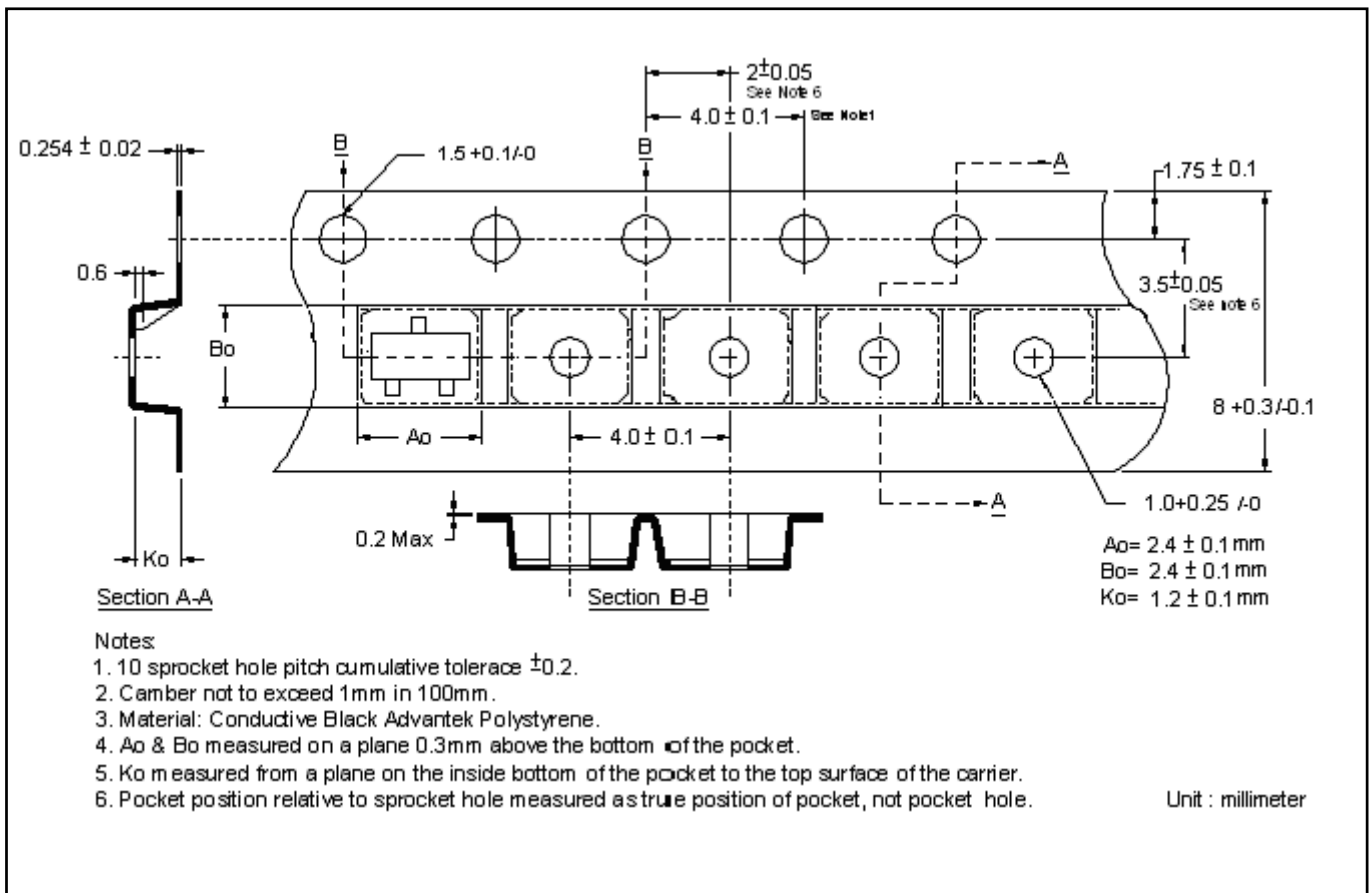
## Recommended Footprint



**Reel Dimension**



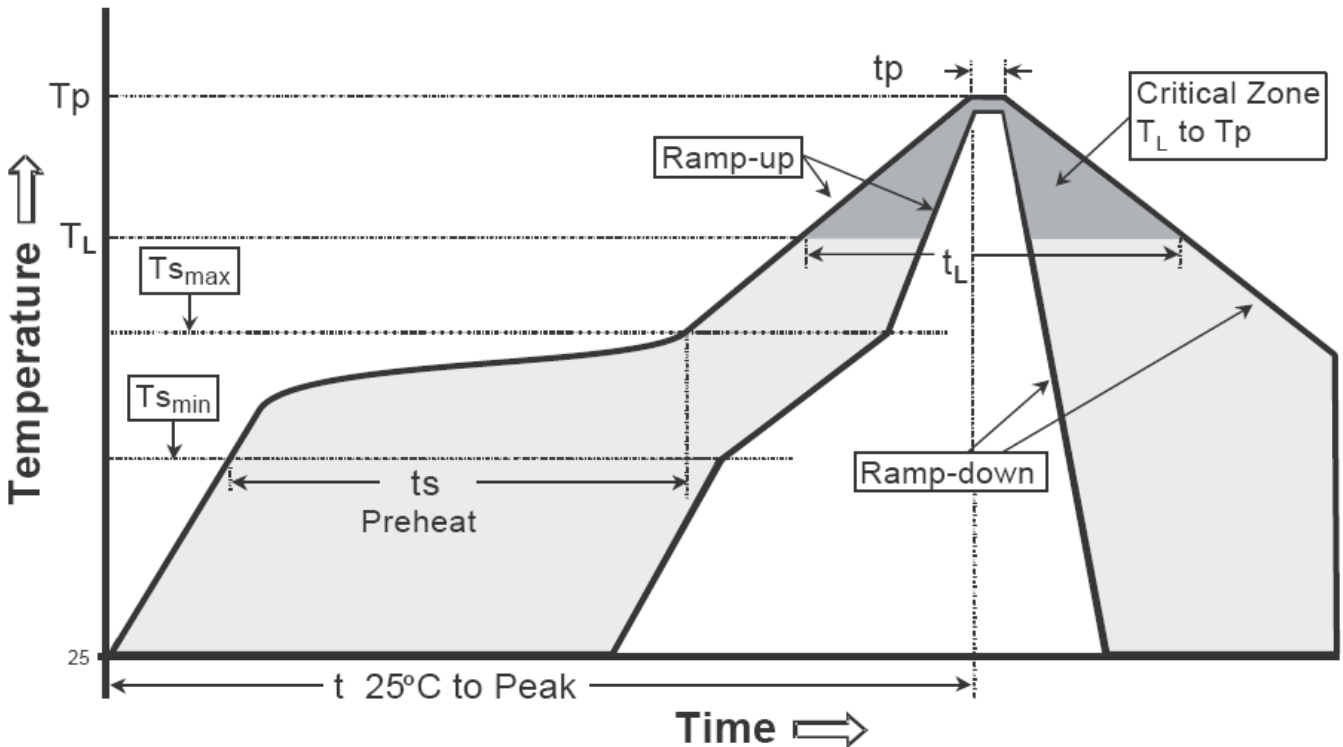
**Carrier Tape Dimension**



**Recommended wave soldering condition**

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

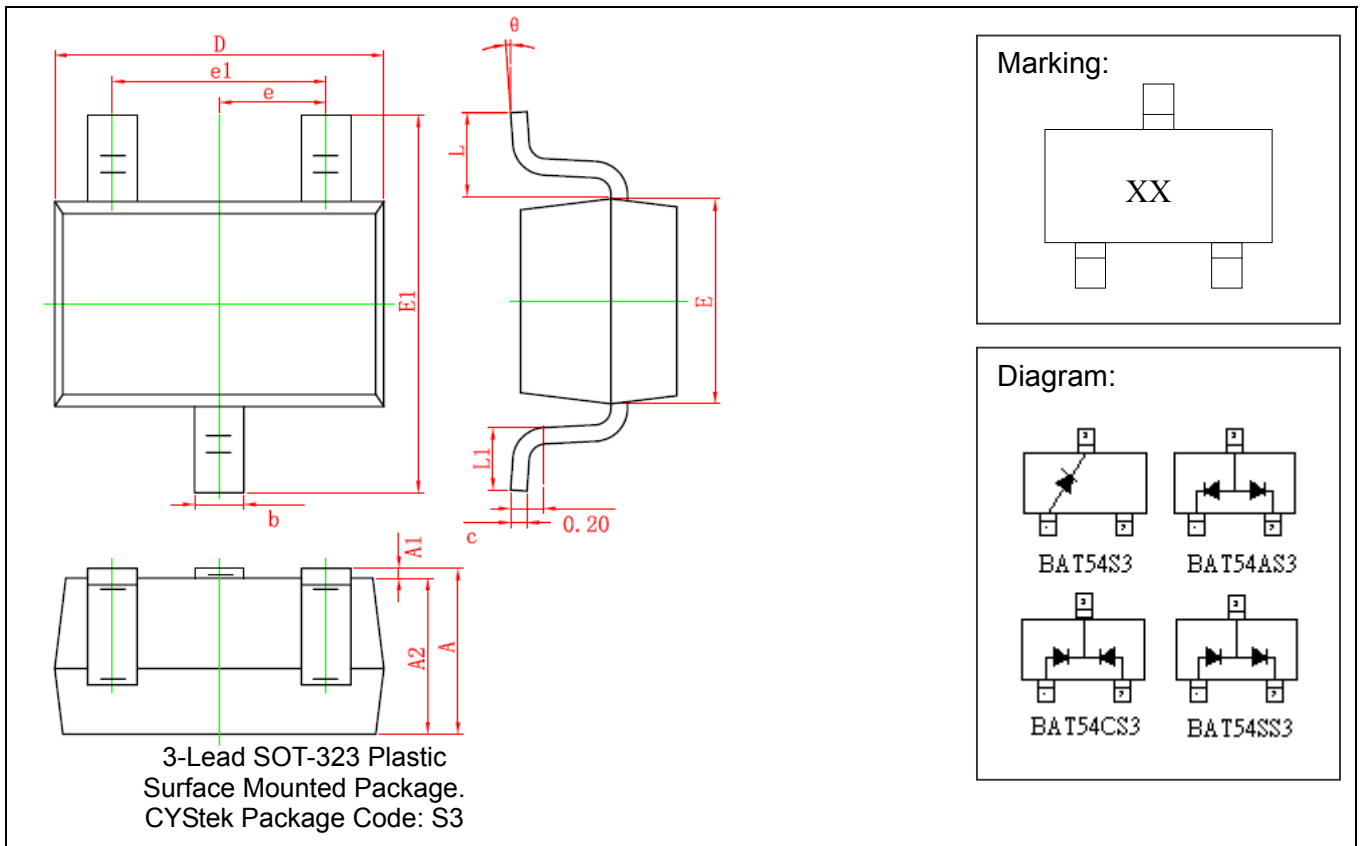
**Recommended temperature profile for IR reflow**



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T <sub>smax</sub> to T <sub>p</sub> )	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T <sub>s min</sub> )	100°C	150°C
-Temperature Max(T <sub>s max</sub> )	150°C	200°C
-Time(t <sub>s min</sub> to t <sub>s max</sub> )	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T <sub>L</sub> )	183°C	217°C
- Time (t <sub>L</sub> )	60-150 seconds	60-150 seconds
Peak Temperature(T <sub>p</sub> )	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

**SOT-323 Dimension**



3-Lead SOT-323 Plastic Surface Mounted Package.  
 CYStek Package Code: S3

- BAT54 S3 : Single Diode (Marking Code B4)
- BAT54AS3 : Common Anode. (Marking Code B7)
- BAT54CS3 : Common Cathode. (Marking Code 5C)
- BAT54SS3 : Series Connected. (Marking Code B8)

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043	E1	2.150	2.450	0.085	0.096
A1	0.000	0.100	0.000	0.004	e	0.650	TYP	0.026	TYP
A2	0.900	1.000	0.035	0.039	e1	1.200	1.400	0.047	0.055
b	0.200	0.400	0.008	0.016	L	0.525	REF	0.021	REF
c	0.080	0.150	0.003	0.006	L1	0.260	0.460	0.010	0.018
D	2.000	2.200	0.079	0.087	θ	0°	8°	0°	8°
E	1.150	1.350	0.045	0.053					

- Notes:**
- Controlling dimension: millimeters.
  - Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
  - If there is any question with packing specification or packing method, please contact your local CYStek sales office.

**Material:**

- Lead: Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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